



Dehydrogenation at the Fe/Lu₂O₃ interface upon rapid thermal annealing

R. Mantovan^{a,*}, C. Wiemer^a, A. Lamperti^a, A. Zenkevich^b, Yu. Lebedinski^b, M. Fanciulli^{a,c}

^a Laboratorio Nazionale MDM CNR-INFM, Via C. Olivetti 2, 20041 Agrate Brianza (MI), Italy

^b Moscow Engineering Physics Institute, 115409 Moscow, Russia

^c Dipartimento di Scienza dei Materiali, Università di Milano Bicocca, Milano, Italy

ARTICLE INFO

Article history:

Received 4 July 2008

Received in revised form

21 January 2009

Available online 26 February 2009

PACS:

68.35.ct

81.40.Ef

76.80.+y

75.70.Cn

61.10.Ht

Keywords:

Interface

Intermetallic

Conversion electron Mössbauer spectroscopy

Thermal annealing

ABSTRACT

The interfaces between ferromagnetic electrodes and tunnel oxides play a crucial role in determining the performances of spin-based electronic devices, such as magnetic tunnel junctions. Therefore, a deep knowledge of the structural, chemical, and magnetic properties of the buried interfaces is required. We study the influence of rapid thermal annealing treatments up to 500 °C on the interfacial properties of the Fe/Lu₂O₃ system. As-grown stacks reveal the presence of hydrogenated Fe–Lu–H intermetallic phases at the Fe/Lu₂O₃ interface most likely due to the H absorption on the Lu₂O₃ surface upon exposure to air and/or to the oxide growth. The annealing treatments induce remarkable changes of the structural, chemical, and magnetic properties at the interface, as evidenced at the atomic scale by the sub-monolayer sensitivity of conversion electron Mössbauer spectroscopy. The use of complementary techniques such as X-ray diffraction, time-of-flight secondary ion mass spectrometry, and *in situ* X-ray photoelectron spectroscopy, confirms that the main effect of the annealing is to gradually promote the dehydrogenation at the Fe/Lu₂O₃ interface.

© 2009 Elsevier B.V. All rights reserved.

1. Introduction

The study of the Fe/oxide interfaces properties at the atomic scale represents a fundamental step towards their efficient inclusion in novel spin-based electronic devices, such as magnetic tunnel junctions (MTJs) [1]. A MTJ stack includes two ferromagnetic (FM) layers separated by a tunnel barrier. The chemical bonding at the FM/oxide interfaces and the interfacial density of states dramatically influence the MTJ performances, while the presence of paramagnetic layers at the interface has a detrimental effect on the tunnel magnetoresistance (TMR) [2]. A deep knowledge of the structural and magnetic properties of the buried interfaces is, therefore, required for a better engineering of MTJ devices.

We have already reported the study of as-deposited interfaces between Fe and different oxides (Al₂O₃, ZrO₂, HfO₂, and Lu₂O₃) [3]. These interfaces have been compared by considering the Fe atoms reactivity at the interface (intermixing), as estimated by conversion electron Mössbauer spectroscopy (CEMS) [3]. We found that the largest intermixing occurs at the Fe/Lu₂O₃ interface, and we

attributed this result to the formation of intermetallic phases and hydrogenated intermetallic compounds [2]. The rapid thermal annealing (RTA) processes are known to be beneficial for improving the TMR and the thermal stability of MTJs [4]. In this contribution, we use the sub-monolayer sensitivity of CEMS to investigate the structural, chemical, and magnetic changes at the Fe/Lu₂O₃ interface upon RTA. Complementary information is obtained by grazing incidence X-ray diffraction (XRD) and time-of-flight secondary ion mass spectrometry (ToF SIMS). The early stage of the Fe/Lu₂O₃ interface formation is investigated by *in situ* X-ray photoelectron spectroscopy (XPS). Our results show that RTA treatments induce a gradual desorption of hydrogen from the Fe/Lu₂O₃ interface, leaving the α -Fe and the intermetallic Fe–Lu phases in contact with Lu₂O₃.

2. Experimental

The Lu₂O₃ layers (nominal 20 nm thick) are deposited at 360 °C by atomic layer deposition (ALD) on a Si(100) substrate, by using the bis-cyclopentadienyl complex {[C₅H₄(SiM₃)]₂LuCl}₂ and H₂O as Lu and O sources, respectively [5]. The oxide surface roughness is around 2.4 nm, as measured by atomic force microscopy [3]. Pulsed laser deposition (PLD) at room temperature (RT) is used to

* Corresponding author.

E-mail address: roberto.mantovan@mdm.infm.it (R. Mantovan).

deposit a thin ^{57}Fe tracer layer ($\sim 2\text{ nm}$) in contact with Lu_2O_3 , followed by the deposition of ^{54}Fe layer. CEMS is therefore sensitive to the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface, being unaffected by the surface oxidation of Fe. Second sample, only containing the ^{54}Fe isotope (nominal 10 nm Fe), has been prepared for the XRD analyses. From here on, we indicate the sample used for CEMS as $\text{Fe}(20\text{ nm})/\text{Lu}_2\text{O}_3$ and the sample with only ^{54}Fe as $\text{Fe}(10\text{ nm})/\text{Lu}_2\text{O}_3$. A third Lu_2O_3 substrate is used for performing XPS *in situ* during the PLD of a 2 nm thick Fe layer. Following the Fe deposition, this sample has been vacuum annealed *in situ* at 500°C for 3 min , and characterized by XPS with a XSAM-800 spectrometer ($\text{MgK}\alpha$ source, $E = 1253.6\text{ eV}$) coupled with the PLD chamber.

The RTA has been performed in Ar ambient in two separate stages: 300°C for 15 s and 500°C for 15 s , followed by a 6 min cool down. The CEMS and XRD analyses have been performed *ex situ* on corresponding samples before and after each RTA. CEMS has been carried out at RT by using a ^{57}Co source embedded in a Rh matrix (activity $\sim 30\text{ mCi}$ when the measurements were performed), which is moved by a standard constant acceleration drive. The samples are incorporated as electrodes in a parallel-plate avalanche counter, which is filled with 180 mbar of a He-CH_4 counting gas [6]. Operating voltages are around 700 V . The spectra are fitted with the least-squares fitting program NORMOS 90 [7]. The XRD data are taken with an ItalStructures HRD3000 diffractometer equipped with a position sensitive curve detector. The data are analysed by using the software package MAUD [8]. ToF SIMS analysis is performed after RTA at 500°C on the $\text{Fe}(20\text{ nm})/\text{Lu}_2\text{O}_3$ sample, with a IONTOF IV instrument using Ga^+ ions at 25 keV for analysis and Cs^+ ions at 0.5 keV for sputtering.

3. Results and discussion

Fig. 1 shows the CEM-spectra of the as-deposited $\text{Fe}/\text{Lu}_2\text{O}_3$ interface and after RTA at 300 and 500°C . The CEM-spectra evidence the typical Mössbauer sextet of $\alpha\text{-Fe}$, component *a* in Fig. 1(a), showing hyperfine field (B_{hf}) of 33 T due to non-interacting ^{57}Fe atoms, a distribution of magnetically split sextets *b*, and a paramagnetic doublet *c*. The distribution *b* has been attributed to the presence of the LuFe_2 intermetallic phase at the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface, together with the existence of a hydrogenated intermetallic compound LuFe_2H_x [3]. The incorporation of H at the interface has been attributed to the two-step process necessary to deposit the Fe layer by PLD on top of the Lu-oxide, which is exposed to air following the ALD and/or the ALD process itself [3]. The doublet *c* is possibly related to a small fraction ($\sim 2\%$) of a binary Fe–Lu amorphous alloy [3]. When compared with the CEM-spectrum reported in Ref. [3] for the same sample, we now use a larger velocity scale. Some additional contributions coming from sextets having $B_{\text{hf}} \geq 33\text{ T}$ are now identified in the distribution *b*. Similar increase of B_{hf} for Fe atoms in contact with oxide layers has been previously observed [9]. To exclude the presence of any FeO_x magnetic oxides, spectra with an even larger velocity scale were recorded (not shown). In fact, the presence of Fe_2O_3 and/or Fe_3O_4 could be easily detected as the CEM-spectra of these phases are characterized by magnetically split sextets having B_{hf} around 50 T [10]. These phases are not detected at the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface either on the as-deposited or on the annealed samples. According to CEMS results, the RTA at 300°C is beneficial in reducing the relative fraction (of the total spectral area) of the distribution *b* from $\sim 71\%$ to 58% , Fig. 1(b). In particular, we observe a large decrease of the contribution from the components having the B_{hf} in the $25\text{--}30\text{ T}$ range, which are related to the hydrogenated LuFe_2H_x . Further, a drastic decrease of the intermixing at the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface is observed after the RTA at

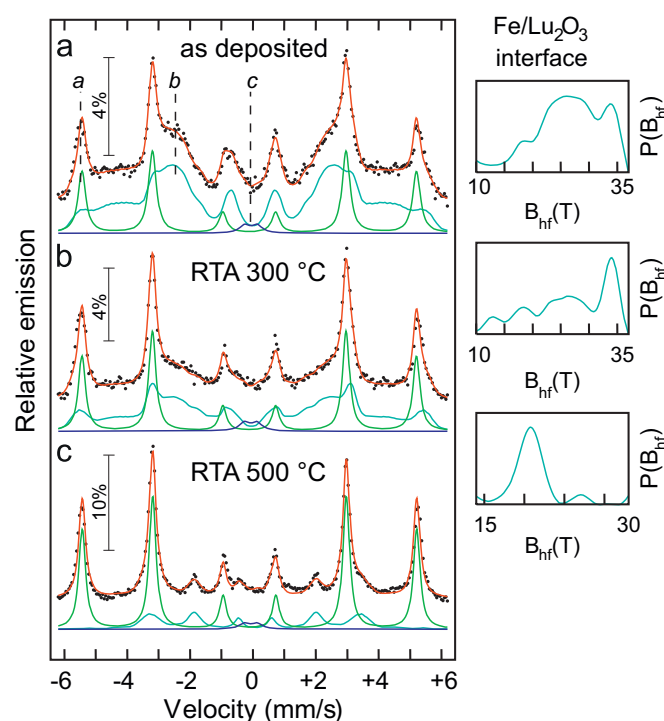


Fig. 1. (Colour online) (a) CEM-spectrum of the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface as-deposited and after (b) RTA at 300°C and (c) RTA at 500°C . CEMS detects the presence of $\alpha\text{-Fe}$, ($\text{LuFe}_2 + \text{LuFe}_2\text{H}_x$), and a small fraction of Lu-rich Lu–Fe phase, as indicated in the figure with *a*, *b*, and *c*, respectively.

500°C , when the spectral contribution from the distribution *b* is reduced to 22% of the total intensity, Fig. 1(c). This is attributed to the almost complete disappearance of the hydrogenated intermetallic contribution from the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface. The CEMS results are substantiated by the XRD, ToF SIMS, and XPS analyses as discussed later. After RTA at 500°C , the main peak in the B_{hf} distribution is around 20 T , which is very close to the B_{hf} observed by Mössbauer spectroscopy for the LuFe_2 crystalline compound at RT [11]. The spectral area of component *c* remains almost constant throughout the RTA treatments. The isomer shift and the quadrupole splitting values of the *a*, *b*, and *c* components in the CEM-spectra after RTA do not show any significant difference with respect to those observed for the as-deposited interface [3].

The XRD spectrum for the as-deposited $\text{Fe}(10\text{ nm})/\text{Lu}_2\text{O}_3$ sample, shown in Fig. 2(a), reveals characteristic features of the diffraction patterns of Lu_2O_3 , $\alpha\text{-Fe}$, LuFe_2 , $\text{LuO}(\text{OH})$, and LuFe_2H_3 further supporting the presence of hydrogenated compounds at the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface [12]. Following the RTA at 300 and 500°C , XRD shows a gradual decrease of the contributions from the hydrogenated compounds confirming the CEMS results, Fig. 2(b). Although a slight reduction of the Lu_2O_3 lattice parameter (within 0.2%) cannot be excluded, the main effect of the 500°C annealing on the diffraction pattern is the reduction of the $\text{LuO}(\text{OH})$ and LuFe_2H_3 related components.

We performed ToF SIMS analysis on the $\text{Fe}(20\text{ nm})/\text{Lu}_2\text{O}_3$ sample after RTA at 500°C , and the results are reported in Fig. 3. The uniform distribution of the OH signal through the Fe and Lu_2O_3 layers, strongly supports the hypothesis for a dehydrogenation process taking place at the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface, as suggested by CEMS. ToF SIMS evidences also a partial interdiffusion at the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface. This aspect could be crucial in view of the inclusion of the $\text{Fe}/\text{Lu}_2\text{O}_3$ system in devices such as MTJs, and is currently under investigation.

To further investigate the structural modifications taking place at the $\text{Fe}/\text{Lu}_2\text{O}_3$ interface, we have performed *in situ* XPS during

Download English Version:

<https://daneshyari.com/en/article/1803421>

Download Persian Version:

<https://daneshyari.com/article/1803421>

[Daneshyari.com](https://daneshyari.com)